TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

# HN2S02FU

### **High Speed Switching Application**

HN2S02FU is composed of 3 independent diodes.

Low forward voltage: V<sub>F (3)</sub> = 0.54V (typ.)

• Low reverse current: I<sub>R</sub> = 5μA (max.)

### **Maximum Ratings (Ta = 25°C)**

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	$V_{RM}$	45	V
Reverse voltage	V <sub>R</sub>	40	V
Maximum (peak) forward current	I <sub>FM</sub>	300 *	mA
Average forward current	Io	100 *	mA
Surge current (10ms)	I <sub>FSM</sub>	1 *	Α
Power dissipation	Р	200 **	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	−55~125	°C
Operating temperature range	T <sub>opr</sub>	<b>−40~100</b>	°C

<sup>\* :</sup> This is maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 ro 3 diodes, the maximum ratings per diodes is 75 % of the single diode one.

# 1. CATHODE 2. CATHODE 3. CATHODE 4. ANODE 5. ANODE US6 6. ANODE JEDEC JEITA TOSHIBA 1. Unit: mm

Weight: 6.2mg(Typ.)

### Electrical Characteristics (Q1, Q2, Q3 Common, Ta = 25°C)

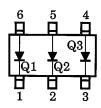
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> = 1mA	_	0.28	_	
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA		0.36	_	V
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA	_	0.54	0.60	
Reverse current	I <sub>R</sub>	_	V <sub>R</sub> = 40V			5	μΑ
Total capacitance	C <sub>T</sub>	_	V <sub>R</sub> = 0, f = 1MH <sub>z</sub>	_	18	_	pF

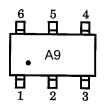
2004-03-01

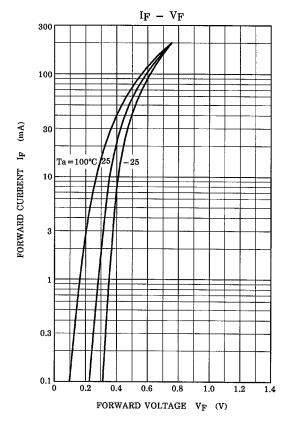
<sup>\*\* :</sup>Total rating

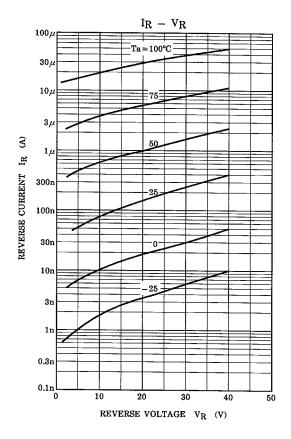
## Pin Assignment (Top View)

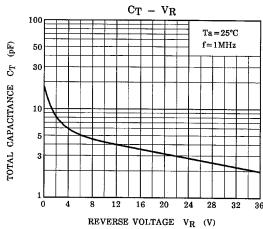
### Marking

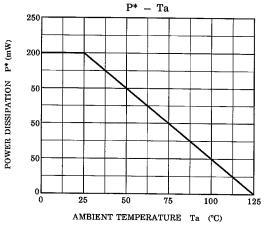












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